

SPTECH Silicon PNP Power Transistor

2SA1859

DESCRIPTION

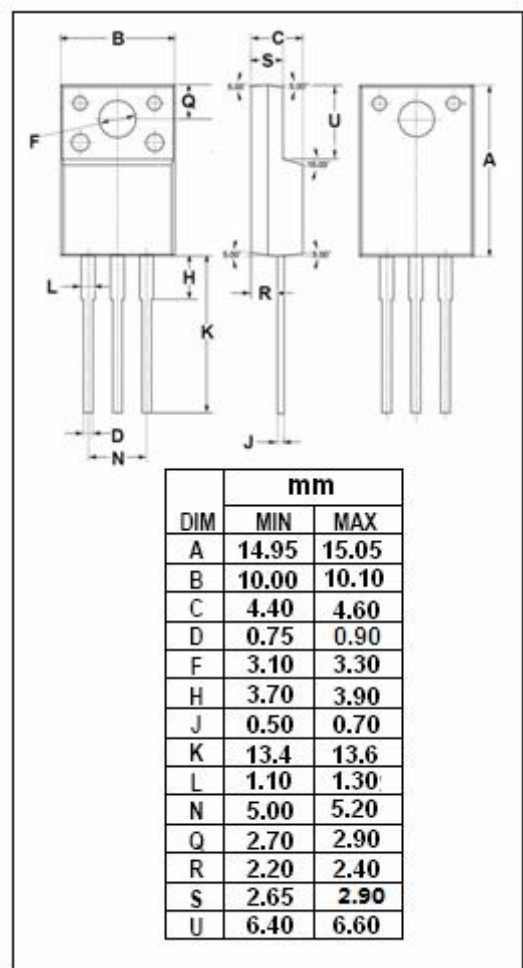
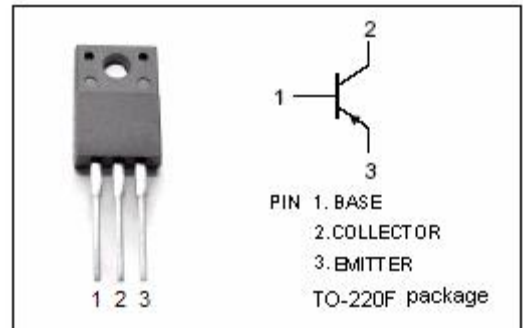
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min})$
- Complement to Type 2SC4883

APPLICATIONS

- Designed for audio output driver and TV velocity-modulation applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	20	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; I _B = 0	-150			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.7A; I _B = -70mA			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V ; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -6V; I _C = 0			-10	μ A
h _{FE}	DC Current Gain	I _C = -0.7A; V _{CE} = -10V	60		240	
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		30		pF
f _T	Current-Gain—Bandwidth Product	I _E = 0.7A; V _{CE} = -12V		60		MHz

Switching Times

t _{on}	Turn-on Time	I _C = -1A, R _L = 20 Ω, I _{B1} = -I _{B2} = -0.1A, V _{CC} = -20V		0.5		μ s
t _{stg}	Storage Time			1.0		μ s
t _f	Fall Time			0.5		μ s